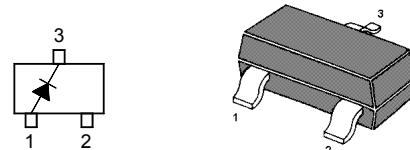


BAS16

Silicon Epitaxial Planar Switching Diode

Features

- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance



Marking Code: 5D
SOT-23 Plastic Package

Applications

- Ultra high speed switching application

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	85	V
Continuous Reverse Voltage	V_R	75	V
Continuous Forward Current	I_F	215	mA
Repetitive Peak Forward Current	I_{FRM}	500	mA
Non-Repetitive Peak Forward Surge Current $t = 1 \mu\text{s}$ $t = 1 \text{ ms}$ $t = 1 \text{ s}$	I_{FSM}	4 1 0.5	A
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-65 to +150	°C

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 1 \text{ mA}$ at $I_F = 10 \text{ mA}$ at $I_F = 50 \text{ mA}$ at $I_F = 150 \text{ mA}$	V_F	- - - -	715 855 1 1.25	mV mV V V
Reverse Current at $V_R = 25 \text{ V}$ at $V_R = 75 \text{ V}$ at $V_R = 25 \text{ V}, T_j = 150^\circ\text{C}$ at $V_R = 75 \text{ V}, T_j = 150^\circ\text{C}$	I_R	- - - -	30 1 30 50	nA μA μA μA
Reverse Breakdown Voltage at $I_R = 100 \text{ μA}$	$V_{(BR)R}$	75	-	V
Diode Capacitance at $V_R = 0$, $f = 1 \text{ MHz}$	C_d	-	2	pF
Reverse Recovery Time at $I_F = 10 \text{ mA}, V_R = 6 \text{ V}, I_{RR} = 1 \text{ mA}, R_L = 100 \Omega$	t_{rr}	-	4	ns

TOP DYNAMIC



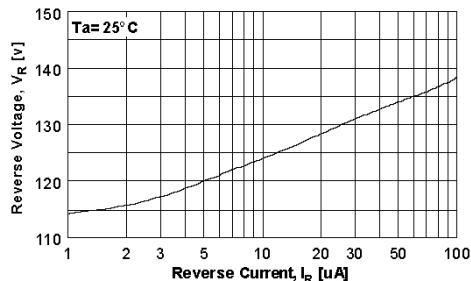


Figure 1. Reverse Voltage vs Reverse Current
BV - 1.0 to 100 uA

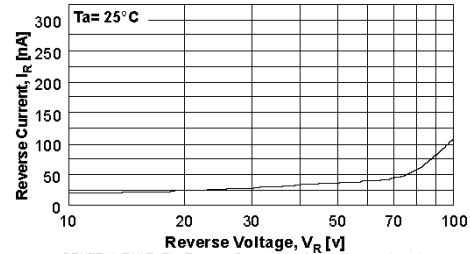


Figure 2. Reverse Current vs Reverse Voltage
IR - 10 to 100 V

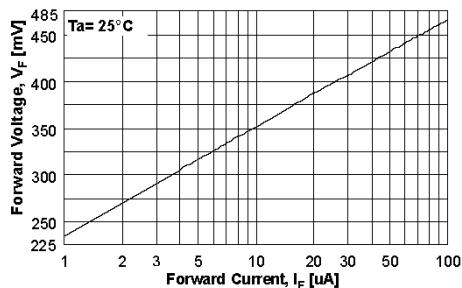


Figure 3. Forward Voltage vs Forward Current
VF - 1.0 to 100 uA

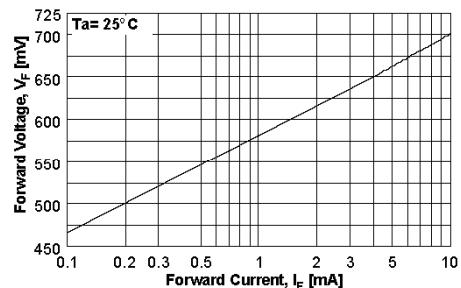


Figure 4. Forward Voltage vs Forward Current
VF - 0.1 to 10 mA

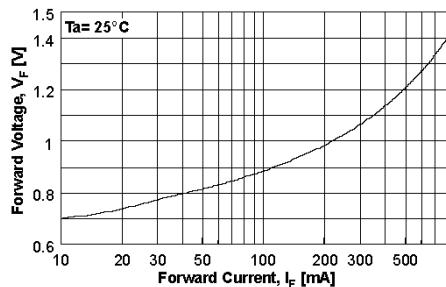


Figure 5. Forward Voltage vs Forward Current
VF - 10 - 800 mA

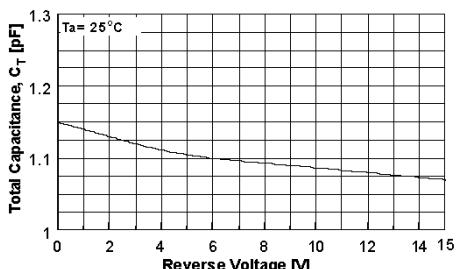


Figure 6. Total Capacitance

